L Number	Hits	Search Text	DB	Time stamp
12	0	438/255,258,201,261,257,756,757,724.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:10
16	36	257/$.ccls. and ((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:10
17	182	semiconductor and ((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:10
18	20	semiconductor and (((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:10
19	22	semiconductor and (((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:10
10	1	438/255,258,201,261,257,756,757,724.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:10
11	4	438/255,258,201,261,257,756,757,724.ccls. and ((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:11
13	9	438/$.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:13
20	0	20020061658.URPN.	USPAT	2004/09/10 09:13
14	10	438/$.ccls. and (((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:15
15	32	438/$.ccls. and ((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:16
-	3	(("6004847") or ("5104819") or ("6274428")).PN.	USPAT	2004/07/26 14:05
-	524	(438/255).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:08
-	479	(438/258).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:10
-	271	(438/261).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:10

-	1104	(438/257).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:10
-	450	(438/756).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:11
-	116	(438/757).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:11
-	308	(438/724).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:11
-	3039	438/255,258,201,261,257,756,757,724.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:15
-	14	438/255,258,201,261,257,756,757,724.ccls. and (ONS or (oxide adj nitride adj silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/10 09:06
-	1	438/255,258,201,261,257,756,757,724.ccls. and ((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/01 10:18
-	24	(ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 14:00
-	13	((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:07
-	8	(("6004847") or ("5104819") or ("6274428") or ("6180457") or ("6429470") or ("6318267") or ("5572050") or ("4775549")).PN.	USPAT	2003/04/07 12:58
-	20	((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and (photoresist or mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 08:00
-	10	(((ONS or (oxide adj nitride adj silicon)) same (ONO or (oxide adj nitride adj oxide))) and (photoresist or mask)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 10:10
-	191	(438/201).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/04 11:17
-	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon)) same (photoresist or mask)) and (re-oxidiz$6 or (second adj oxidiz$6))	USPAT; JPO	2003/04/07 12:34
-	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz$6 or (second adj oxidiz$6))	USPAT; JPO	2003/04/07 12:38

-	0	(ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon)) and (photoresist or mask) and (re-oxidiz$6 or (second adj oxidiz$6)) and semiconductor	USPAT; JPO	2003/04/07 12:38
-	66	(ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))	USPAT; JPO	2003/04/07 12:38
-	80283	(ONO or (oxide adj nitride adj oxide)) or (ONS or (oxide adj nitride adj silicon))	USPAT; JPO	2003/04/07 12:38
-	23	(ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))	USPAT; JPO	2003/04/07 12:38
-	0	((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz$6 or (second adj oxidiz$6))	USPAT; JPO	2003/04/07 12:39
-	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz$6 or (second adj oxidiz$6))	USPAT; JPO	2003/04/07 12:41
-	11	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and semiconductor	USPAT; JPO	2003/04/07 12:40
-	22	((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and semiconductor	USPAT; JPO	2003/04/07 12:40
-	36	((ONO or (oxide adj nitride adj oxide)) or (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (re-oxidiz$6 or (second adj oxidiz$6))	USPAT; JPO	2003/04/07 12:40
-	0	((ONO or (oxide adj nitride adj oxide)) same (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (second adj oxidiz$6)	USPAT; JPO	2003/04/07 12:41
-	0	((ONO or (oxide adj nitride adj oxide)) and (ONS or (oxide adj nitride adj silicon))) and (photoresist or mask) and (second adj oxidiz$6)	USPAT; JPO	2003/04/07 12:41
-	10	(("5756376") or ("5770467") or ("6318267") or ("6004847") or ("6429470") or ("6180457") or ("5104819") or ("5572050") or ("6472259") or ("4775549")).PN.	USPAT	2003/04/08 09:24
-	1	("5650344").PN.	USPAT	2003/04/08 09:37
-	5	(("5650344") or ("4698787") or ("4543597") or ("5049514") or ("5083172")).PN.	USPAT	2003/04/08 09:38
-	8	(("6225162") or ("6388305") or ("6168987") or ("6133602") or ("5591681") or ("5436481") or ("6133093") or ("6096604")).PN.	USPAT	2003/04/18 13:51
-	9	(("6225162") or ("6388305") or ("6168987") or ("6133602") or ("5591681") or ("5436481") or ("6133093") or ("6096604") or ("5572050")).PN.	USPAT	2003/04/18 15:09
-	1	("6004847").PN.	USPAT	2003/09/30 13:31
-	150	438/$.ccls. and (oxide adj nitride adj silicon) and (photoresist or resist or mask) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 13:38
-	100	438/$.ccls. and (oxide adj nitride adj silicon) and (photoresist) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 10:58
-	21	438/$.ccls. and ((oxide adj nitride adj silicon) same (photoresist)) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 11:08

-	13829	438/$.ccls. and ((silicon) same (photoresist)) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 13:35
-	13	438/255,258,201,261,257,756,757,724.ccls. and (ONS or (oxide adj nitride adj silicon)) and (photoresist or resist or mask) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 11:11
-	3	438/255,258,201,261,257,756,757,724.ccls. and ((oxide adj nitride adj silicon) same (photoresist or resist or mask)) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 11:20
-	1	("4376672").PN.	USPAT	2003/09/30 13:43
-	982	438/255,258,201,261,257,756,757,724.ccls. and ((silicon) same (photoresist)) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 13:35
-	265	438/$.ccls. and (ONS or (oxide adj nitride adj silicon)) and (photoresist or resist or mask) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 07:57
-	10826	nguyen.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 13:38
-	51	nguyen.inv. and (bich-yen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 13:38
-	51	(nguyen.inv. and (bich-yen)) and motorola	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/30 13:38
-	2	(("4376672") or ("5665620")).PN.	USPAT	2003/09/30 13:49
-	9	(("4376672") or ("5665620") or ("6472259") or ("5104819") or ("6180457") or ("6168987") or ("5591681") or ("6096604") or ("5358892")).PN.	USPAT	2003/09/30 14:02
-	1	("20020117736").PN.	US-PGPUB	2003/09/30 14:07
-	18265	438/$.ccls. and (ONS or (oxide same nitride same silicon)) and (photoresist or resist or mask) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 07:58
-	2092	438/255,258,201,261,257,756,757,724.ccls. and (ONS or (oxide same nitride same silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 07:59
-	2090	438/255,258,201,261,257,756,757,724.ccls. and (oxide same nitride same silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 07:59
-	585	438/255,258,201,261,257,756,757,724.ccls. and ((oxide same nitride same silicon) same photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 08:01
-	537	438/255,258,201,261,257,756,757,724.ccls. and ((oxide same nitride same silicon) same photoresist) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 08:09

–	537	438/255,258,201,261,257,756,757,724.ccls. and ((ONS or (oxide same nitride same silicon)) same photoresist) and @ad<=20011130	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 08:25
–	0	438/255,258,201,261,257,756,757,724.ccls. same (high adj voltage adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 14:26
–	11	438/255,258,201,261,257,756,757,724.ccls. and (high adj voltage adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 14:27
–	11	438/255,258,201,261,257,756,757,724.ccls. and (high adj voltage adj oxide) and @ad<=20011120	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/01 14:27
–	36	(("ONS") or (oxide adj nitride adj silicon)) same (("ONO") or (oxide adj nitride adj oxide)) and @ad<=20011120	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 14:01
–	19	((oxide adj nitride adj silicon) or ("ONS")) with ((oxide adj nitride adj oxide) or ("ONO")) and @ad<=20011120	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/26 14:03
–	36	((oxide adj nitride adj silicon) or ("ONS")) same ((oxide adj nitride adj oxide) or ("ONO")) and @ad<=20011120	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 07:07
–	0	20020061658.URPN.	USPAT	2004/07/27 07:02
–	1689	((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO")) and @ad<=20011120	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 07:09
–	159	((oxide adj nitride adj silicon) or ("ONS")) and ((oxide adj nitride adj oxide) or ("ONO")) and @ad<=20011120 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/27 07:10